

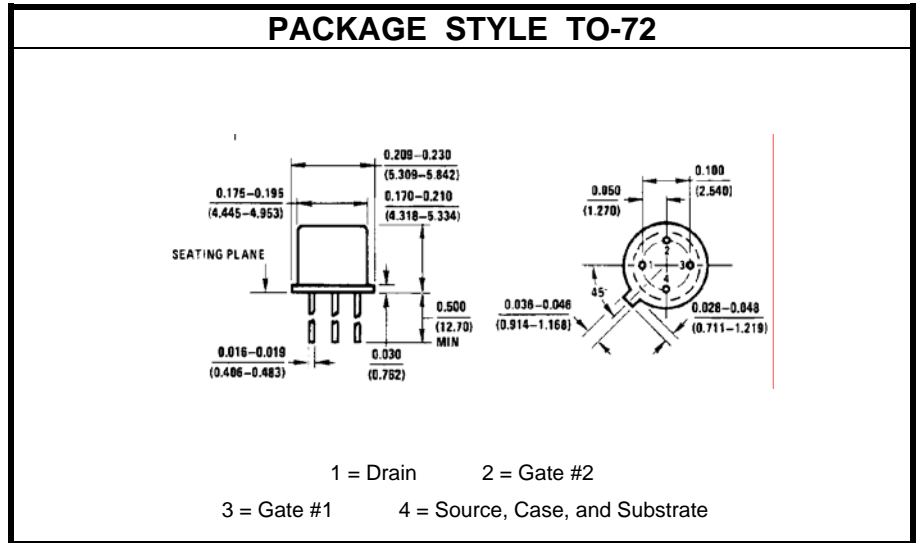
MOS FIELD-EFFECT TRANSISTOR

DESCRIPTION:

The **ASI 40822** is a N-Channel Dual-Gate Depletion Type Transistor With Monolithic Gate Protection Diodes, used in RF, IF Amplifier and Mixer Applications up to 150 MHz.

MAXIMUM RATINGS

I_D	50 mA
V_D	24 V
P_{DISS}	330 mW @ T _A = 25 °C
T_J	-65 °C to +175 °C
T_{STG}	-65 °C to +175 °C



CHARACTERISTICS T_A = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
V_{G1S(OFF)}	V _{DS} = 15 V V _{G2S} = 4.0 V I _D = 50 μA		-2.0	-4.0	V
V_{G2S(OFF)}	V _{DS} = 15 V V _{G1S} = 0 V I _D = 50 μA		-2.0	-4.0	V
I_{G1SSF}	V _{G1S} = 6.0 V V _{G2S} = V _{DS} = 0 V			50	μA
I_{G1SSR}	V _{G1S} = -6.0 V V _{G2S} = V _{DS} = 0 V			50	μA
I_{G2SSF}	V _{G2S} = 6.0 V V _{G1S} = V _{DS} = 0 V			50	μA
I_{G2SSR}	V _{G2S} = -6.0 V V _{G1S} = V _{DS} = 0 V			50	μA
I_{DS}	V _{DS} = 15 V V _{G1S} = 0 V V _{G2S} = 4.0 V	5.0	15	30	mA
V_{(BR)G1}	I _{G1} = ±100 μA		9.0		V
V_{(BR)G2}	I _{G2} = ±100 μA		9.0		V
g_{fs}	V _{DS} = 15 V V _{G2S} = 4.0 V I _D = 10 mA f = 1.0 KHZ		12000		μmho
C_{rSS} C_{iSS} C_{oss}	V _{DS} = 15 V V _{G2S} = 4.0 V I _D = 10 mA f = 1.0 MHz	0.005	6.5 2.0	0.03 9.5	pF
G_{PS} NF	V _{DS} = 15 V V _{G2S} = 4.0 V I _D = 10 mA f = 200 MHz	19	24 2.0	3.5	dB